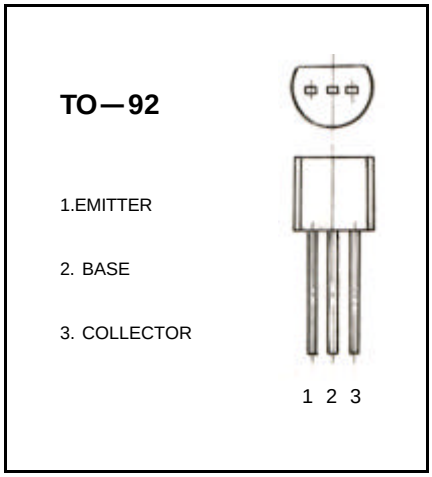
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

M8550 TRANSISTOR (PNP)



FEATURES

Power dissipation

P_{CM} : 0.625 W (Tamb=25℃)

Collector current

I_{CM} : -1 A

Collector-base voltage

$V_{(BR)CBO}$: -40 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= -100μA, I_E=0	-40		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$*	I_C= -0.1mA, I_B=0	-25		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= -100μA, I_C=0	-6		V
Collector cut-off current	I_{CBO}	V_{CB}= -35V, I_E=0		-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}= -20V, I_B=0		-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-1V, I_C=-5mA	45		
	$h_{FE(2)}$	V_{CE}=-1V, I_C=-100mA	85	300	
	$h_{FE\ (3)}$	V_{CE}=-1V, I_C=-800mA	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -800mA, I_B=-80mA		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-800mA, I_B=-80mA		-1.2	V
Transition frequency	f_T	V_{CE}=-6V, I_C= -20mA f=30MHz	150		MHz

* Pulse Test : pulse width ≤ 300μs, duty cycle ≤2%.